

Interlace Operation in TI Virtual-Phase CCD Image Sensors

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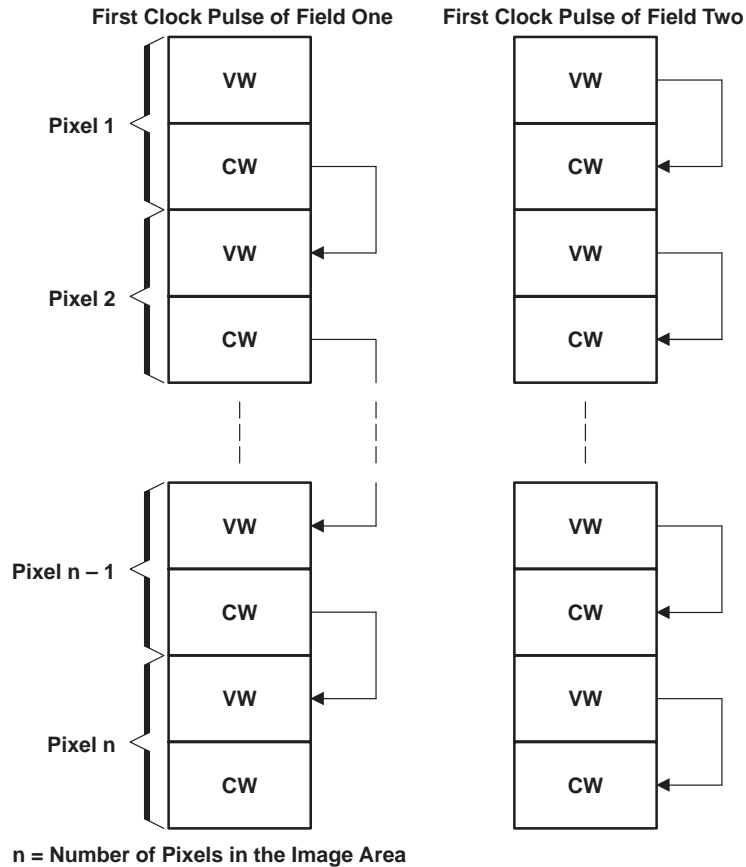


Figure 1. Virtual-Phase Pixel Structure and Centroid Shift

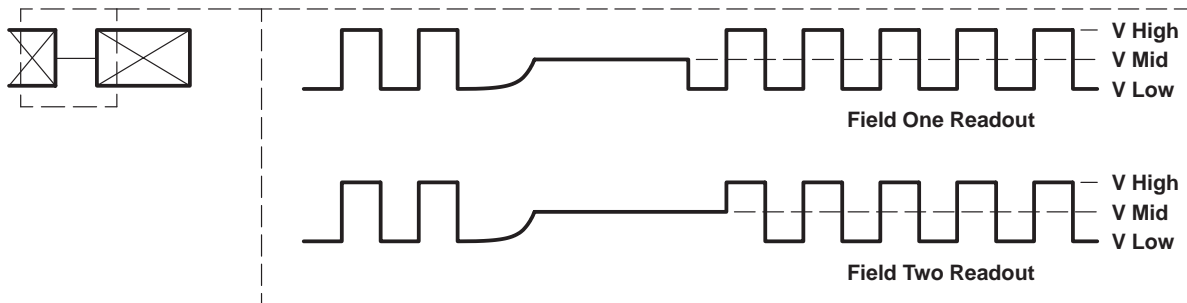


Figure 2. Image-Area Gate Timing for Interlace

- NOTES:
- A. Interlace operation is obtained by performing a centroid shift on the virtual-phase pixels.
 - B. The centroid shift is obtained by holding the image-area gate at mid-level during integrate time and making a mid-to-low transition at the start of field one and then making a mid-to-high transition at the start of field two.
 - C. Optimum midlevel for the image-area gate (IAG) is obtained when the charge is equally distributed between the virtual well (vW) and the clocked well (cW).
 - D. Antiblooming needs to be clocked for interlace to work.
 - E. Adjustment is as follows:
 - IAG midlevel should be low (about -10 V). AB+ should be low (about 0 V).
 - While viewing a saturated target, increase AB+ until the signal is 35% of full well.
 - Increase IAG midlevel until the signal doubles.

